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<ul> <li>Function, Pinout, and Drive Compatible With FCT, F Logic, and AM29821</li> </ul>	P, Q, OR SO PACKAGE (TOP VIEW)
<ul> <li>Reduced V<sub>OH</sub> (Typically = 3.3 V) Version of Equivalent FCT Functions</li> </ul>	$ \begin{array}{c c} \hline OE & \hline 1 & 24 \\ \hline D_0 & 2 & 23 \\ \hline \end{array} \\ V_{0} \\ \hline \end{array} $
<ul> <li>Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics</li> </ul>	$     D_1 \begin{bmatrix} 3 & 22 \end{bmatrix} Y_1 \\     D_2 \begin{bmatrix} 4 & 21 \end{bmatrix} Y_2 \\     D_3 \begin{bmatrix} 5 & 20 \end{bmatrix} Y_3 $
<ul> <li>I<sub>off</sub> Supports Partial-Power-Down Mode Operation</li> </ul>	$     \begin{array}{ccc}       D_4 & \begin{bmatrix} 6 & 19 \\       T_5 & \end{bmatrix} Y_4 \\       D_5 & \begin{bmatrix} 7 & 18 \\       Y_5 & \end{bmatrix} Y_5     $
Matched Rise and Fall Times	$D_6$ 8 17 Y <sub>6</sub>
<ul> <li>Fully Compatible With TTL Input and Output Logic Levels</li> </ul>	$D_7 [] 9 16 [] Y_7  D_8 [] 10 15 ] Y_8  D_7 [] 11 15 ] Y_8  D_7 [] 10 15 ] Y_8  D_8 [] 10 15 ] Y_8 \\ D_8 [] $
<ul> <li>ESD Protection Exceeds JESD 22</li> <li>2000-V Human-Body Model (A114-A)</li> <li>200-V Machine Model (A115-A)</li> </ul>	D <sub>9</sub> 11 14 Y <sub>9</sub> GND 12 13 CP

- 1000-V Charged-Device Model (C101)
- 64-mA Output Sink Current 32-mA Output Source Current
- High-Speed Parallel Register With Positive-Edge-Triggered D-Type Flip-Flops
- 3-State Outputs

#### description

This bus-interface register is designed to eliminate the extra packages required to buffer existing registers and provide extra data width for wider address/data paths or buses carrying parity. The CY74FCT821T is a 10-bit-wide buffered version of the popular CY74FCT374 function. This device is ideal for use as an output port requiring high I<sub>OL</sub>/I<sub>OH</sub>.

This device is designed for high-capacitance load drive capability, while providing low-capacitance bus loading at both inputs and outputs. Outputs are designed for low-capacitance bus loading in the high-impedance state.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

NAME	I/O	DESCRIPTION										
D	Ι	D flip-flop data inputs										
CP	0	Clock pulse for the register. Enters data into the register on the low-to-high clock transition.										
Y	0	Register 3-state outputs										
OE	I	Output control. When $\overline{OE}$ is high, the Y outputs are in the high-impedance state. When $\overline{OE}$ is low, true register data is present at the Y outputs.										

PIN DESCRIPTION



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		•=			
TA	PAC	KAGE <sup>†</sup>	SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	QSOP – Q	Tape and reel	6	CY74FCT821CTQCT	FCT821C
	SOIC – SO	Tube	6	CY74FCT821CTSOC	FCT821C
	3010 - 30	Tape and reel	6	CY74FCT821CTSOCT	FGT02TC
	DIP – P	Tube	7.5	CY74FCT821BTPC	CY74FCT821BTPC
-40°C to 85°C	SOIC – SO	Tube	7.5	CY74FCT821BTSOC	FCT821B
	3010 - 30	Tape and reel	7.5	CY74FCT821BTSOCT	FGT02TB
	QSOP – Q	Tape and reel	10	CY74FCT821ATQCT	FCT821A
	SOIC – SO	Tube	10	CY74FCT821ATSOC	FCT821A
	3010 - 30	Tape and reel	10	CY74FCT821ATSOCT	FUIOZIA

#### **ORDERING INFORMATION**

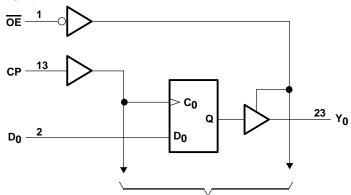
<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE

	INPUTS	;		RNAL PUTS	FUNCTION
OE	D	СР	Q	Y	
Н	Х	Ŷ	L	Z	Z
н	L	$\uparrow$	L	Z	
н	Н	$\uparrow$	н	Z	Load
L	L	$\uparrow$	L	L	LUau
L	Н	$\uparrow$	н	Н	

H = High logic level, L = Low logic level, X = Don't care,  $\uparrow$  = Low-to-high transition, Z = High-impedance state

### logic diagram (positive logic)



**To Nine Other Channels** 



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#### absolute maximum rating over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range to ground potential		
DC input voltage range	0.5	V to 7 V
DC output voltage range	0.5	V to 7 V
DC output current (maximum sink current/pin)		120 mA
Package thermal impedance, $\theta_{JA}$ (see Note 1): P package		67°C/W
(see Note 2): Q package		61°C/W
(see Note 2): SO package		46°C/W
Ambient temperature range with power applied, T <sub>A</sub>	-65°C	to 135°C
Storage temperature range, T <sub>stg</sub>	–65°C 1	to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The package thermal impedance is calculated in accordance with JESD 51-3.

2. The package thermal impedance is calculated in accordance with JESD 51-7.

#### recommended operating conditions (see Note 3)

		MIN	NOM	MAX	UNIT
VCC	Supply voltage	4.75	5	5.25	V
VIH	High-level input voltage	2			V
VIL	Low-level input voltage			0.8	V
ЮН	High-level output current			-32	mA
IOL	Low-level output current			64	mA
TA	Operating free-air temperature	-40		85	°C

NOTE 3: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation.



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## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITION	S	MIN	TYP†	MAX	UNI
VIK	V <sub>CC</sub> = 4.75 V,	I <sub>IN</sub> = -18 mA			-0.7	-1.2	V
Maria		I <sub>OH</sub> = -32 mA		2			v
VOH	V <sub>CC</sub> = 4.75 V	I <sub>OH</sub> = -15 mA		2.4	3.3		v
VOL	V <sub>CC</sub> = 4.75 V,	I <sub>OL</sub> = 64 mA			0.3	0.55	V
V <sub>hys</sub>	All inputs				0.2		V
lj	V <sub>CC</sub> = 5.25 V,	$V_{IN} = V_{CC}$				5	μA
ΙΗ	V <sub>CC</sub> = 5.25 V,	V <sub>IN</sub> = 2.7 V				±1	μA
۱ <sub>IL</sub>	V <sub>CC</sub> = 5.25 V,	V <sub>IN</sub> = 0.5 V				±1	μA
IOZH	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 2.7 V				10	μA
IOZL	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 0.5 V				-10	μA
los‡	V <sub>CC</sub> = 5.25 V,	V <sub>OUT</sub> = 0 V		-60	-120	-225	m/
l <sub>off</sub>	$V_{CC} = 0 V,$	V <sub>OUT</sub> = 4.5 V				±1	μA
ICC	V <sub>CC</sub> = 5.25 V,	$V_{IN} \le 0.2 V$ ,	$V_{IN} \ge V_{CC} - 0.2 V$		0.1	0.2	m
∆ICC	V <sub>CC</sub> = 5.25 V, V <sub>IN</sub> =	= 3.4 V <sup>§</sup> , f <sub>1</sub> = 0, Outputs or	ben		0.5	2	m
ICCD	$\frac{V_{CC}}{OE} = \frac{5.25}{EN} \text{ V, One}$	bit switching at 50% duty c $N \le 0.2$ V or $V_{IN} \ge V_{CC} - 0.2$	ycle, Outputs open, 0.2 V		0.06	0.12	m∕ M⊦
		One bit switching at f <sub>1</sub> = 5 MHz	$\begin{array}{l} V_{IN} \leq 0.2 \ V \ or \\ V_{IN} \geq V_{CC} - 0.2 \ V \end{array}$		0.7	1.4	
IC#	$V_{CC} = 5.25 V,$	at 50% duty cycle	$V_{IN} = 3.4 \text{ V or GND}$		1.2	3.4	m/
	<u>Outputs open,</u> OE = EN = GND	Eight bits switching at f <sub>1</sub> = 2.5 MHz	$\begin{array}{l} V_{IN} \leq 0.2 \ V \ or \\ V_{IN} \geq V_{CC} - 0.2 \ V \end{array}$		1.6	3.2	1117
		at 50% duty cycle	$V_{IN} = 3.4 \text{ V or GND}$		3.9	12.2	
Ci					5	10	pF
Co					9	12	pF

<sup>†</sup> Typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

\* Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests, IOS tests should be performed last.

§ Per TTL-driven input ( $V_{IN}$  = 3.4 V); all other inputs at  $V_{CC}$  or GND

This parameter is derived for use in total power-supply calculations.

<sup>#</sup> IC = ICC +  $\Delta$ ICC × D<sub>H</sub> × N<sub>T</sub> + I<sub>CCD</sub> (f<sub>0</sub>/2 + f<sub>1</sub> × N<sub>1</sub>)

Where:

IC = Total supply current

I<sub>CC</sub> = Power-supply current with CMOS input levels

 $\Delta I_{CC}$  = Power-supply current for a TTL high input (VIN = 3.4 V)

 $D_H$  = Duty cycle for TTL inputs high

 $N_T$  = Number of TTL inputs at  $D_H$ 

I<sub>CCD</sub> = Dynamic current caused by an input transition pair (HLH or LHL)

 $f_0$  = Clock frequency for registered devices, otherwise zero

f<sub>1</sub> = Input signal frequency

N<sub>1</sub> = Number of inputs changing at f<sub>1</sub>

All currents are in milliamperes and all frequencies are in megahertz.

Il Values for these conditions are examples of the ICC formula.



## **CY74FCT821T 10-BIT BUS-INTERFACE REGISTER** WITH 3-STATE OUTPUTS SCCS033B- MAY 1994 - REVISED NOVEMBER 2001

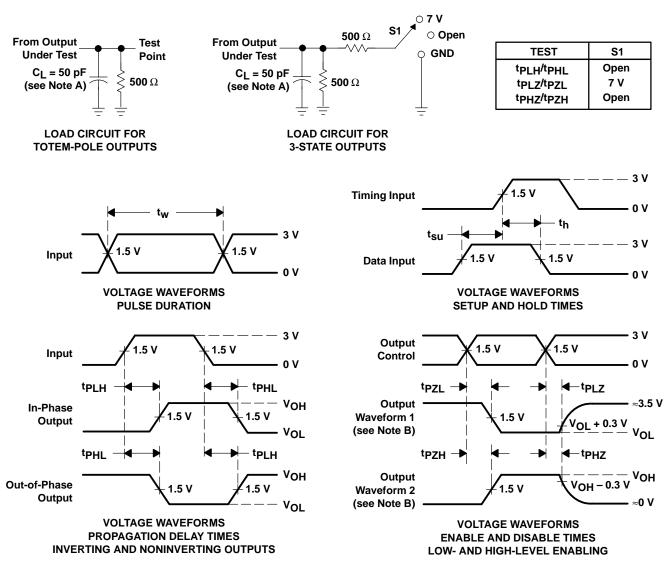
# timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

	PARAMETER	TEST LOAD	CY74FCT821AT		CY74FCT821BT		CY74FCT821CT		UNIT	
	PARAMETER		TEST LOAD	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
tw	Pulse duration	СР	C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500 Ω	7		6		6		ns
t <sub>su</sub>	Setup time, before $CP^\uparrow$	Data	C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500 Ω	4		3		3		ns
th	Hold time, after $CP^\uparrow$	Data	C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500 Ω	2		1.5		1.5		ns

## switching characteristics over operating free-air temperature range (see Figure 1)

PARAMETER	FROM	то	TEST LOAD	CY74FC1	821AT	CY74FCT	821BT	CY74FC1	821CT	UNIT
PARAMETER	(INPUT)	(OUTPUT)	TEST LOAD	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
<sup>t</sup> PLH	СР	Y	CL = 50 pF,		10		7.5		6	
<sup>t</sup> PHL	CF	Ι	$R_L = 500 \Omega$		10		7.5		6	ns
<sup>t</sup> PLH	СР	Y	C <sub>L</sub> = 300 pF,		20		15		12.5	ns
<sup>t</sup> PHL		Ι	RL = 500 Ω		20		15		12.5	115
<sup>t</sup> PZH	OE	Y	C <sub>L</sub> = 50 pF,		12		8		7	ns
<sup>t</sup> PZL	OL	I	RL = 500 Ω		12		8		7	115
<sup>t</sup> PZH	OE	Y	C <sub>L</sub> = 300 pF,		23		15		12.5	ns
<sup>t</sup> PZL	OE	Ι	RL = 500 Ω		23		15		12.5	115
<sup>t</sup> PHZ	OE	v	CL = 5 pF,		7		6.5		6	ns
<sup>t</sup> PLZ	OL	Y	$R_{L} = 500 \Omega$		7		6.5		6	115
<sup>t</sup> PHZ	OE	Y	C <sub>L</sub> = 50 pF,		8		7.5		6.5	ns
<sup>t</sup> PLZ	UE UE	1	R <sub>L</sub> = 500 Ω		8		7.5		6.5	115

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#### PARAMETER MEASUREMENT INFORMATION

NOTES: A. C<sub>1</sub> includes probe and jig capacitance.

 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms





#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(1)				,	(2)	(6)	(3)		(43)	
CY74FCT821ATSOC	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821A	Samples
CY74FCT821BTSOC	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821B	Samples
CY74FCT821CTQCT	ACTIVE	SSOP	DBQ	24	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT821C	Samples
CY74FCT821CTSOC	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C	Samples
CY74FCT821CTSOCT	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT821C	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



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## PACKAGE OPTION ADDENDUM

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Texas

STRUMENTS

#### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	-	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT821CTQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT821CTSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1



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## PACKAGE MATERIALS INFORMATION

5-Dec-2023



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT821CTQCT	SSOP	DBQ	24	2500	356.0	356.0	35.0
CY74FCT821CTSOCT	SOIC	DW	24	2000	350.0	350.0	43.0

#### TEXAS INSTRUMENTS

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### TUBE



## - B - Alignment groove width

#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CY74FCT821ATSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT821BTSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT821CTSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6

DBQ (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.

D. Falls within JEDEC MO-137 variation AE.



DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AD.



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